

IN THE CLAIMS:

Claims 10 through 16, 24 and 25 were previously cancelled. Claims 2-9, 18-23 and 27-31 have been amended herein. All of the pending claims are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

Listing of Claims:

1. (Previously presented) A method of making a cathode assembly of an FED, comprising:
providing a substrate;
forming an emitter electrode structure on the substrate;
forming a resistive layer over the emitter electrode structure;
forming an insulative layer on a portion of the resistive layer;
forming at least one micropoint emitter on the substrate and in contact with both the resistive layer and the insulative layer;
forming a conductive grid structure spaced from the at least one micropoint emitter; and
forming a dielectric structure spaced from the at least one micropoint emitter and between the insulative layer and the grid structure.
2. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the emitter electrode structure comprises metal.
3. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the emitter electrode structure comprises aluminum.
4. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the resistive layer comprises silicon.

5. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the insulative layer comprises silicon oxide.

6. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein ~~said the~~ insulative layer comprises silicon nitride.

7. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the insulative layer comprises a strip having a thickness of about 1000 Å.

8. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein the substrate comprises glass.

9. (Currently amended) The method of ~~Claim 1~~ claim 1, wherein forming the conductive grid structure and the dielectric structure comprise:
depositing a dielectric layer over the insulative layer and the at least one micropoint emitter;
depositing a conductive layer over the dielectric layer; and
selectively etching openings through the conductive and dielectric layers to expose the at least one micropoint emitter, with walls defining the openings being spaced away from the at least one micropoint emitter.

10.-16. (Cancelled)

17. (Previously presented) A method of making a column line structure for an addressing matrix of a field emission device, comprising:
forming an elongated conductive structure on a substrate;
forming a resistive layer directly on a top surface of the elongated conductive structure and over at least a portion of a side surface thereof;
forming an insulative layer covering a top surface of the resistive layer and leaving at least a portion of a side surface thereof exposed; and
forming a micropoint emitter over the substrate in lateral contact with the resistive layer and the insulative layer.

18. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the elongated conductive structure comprises metal.

19. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the elongated conductive structure comprises aluminum.

20. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the resistive layer comprises silicon.

21. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the insulative layer comprises silicon oxide.

22. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the insulative layer comprises silicon nitride.

23. (Currently amended) The method of ~~Claim 17~~ claim 17, wherein the insulative layer comprises a strip having a thickness of about 1000 Å.

24. (Cancelled)

25. (Cancelled)

26. (Previously presented) A method of making an FED, comprising:
making a cathode assembly, making an anode assembly, and assembling the cathode and the
anode assemblies,
wherein making a cathode assembly comprises:
providing a substrate;
forming an emitter electrode structure on the substrate;
forming a resistive layer over the emitter electrode structure;
forming an insulative layer on a portion of the resistive layer;
forming at least one micropoint emitter on the substrate and in contact with both the resistive
layer and the insulative layer;
forming a conductive grid structure spaced from the at least one micropoint emitter; and
forming a dielectric structure spaced from the at least one micropoint emitter and between the
insulative layer and the grid structure.

27. (Currently amended) The method of ~~Claim 26~~ claim 26, wherein the emitter
electrode structure comprises metal strips.

28. (Currently amended) The method of ~~Claim 26~~ claim 26, wherein the emitter
electrode structure comprises aluminum strips.

29. (Currently amended) The method of ~~Claim 28~~ claim 28, wherein the aluminum
strips have a thickness of about 1000 Å.

30. (Currently amended) The method of ~~Claim 26~~ claim 26, wherein the insulative layer comprises silicon oxide.

31. (Currently amended) The method of ~~Claim 26~~ claim 26, wherein the insulative layer comprises silicon nitride.